

Abstract

A III nitride buffer film including at least Al element and having a screw-type dislocation density of $1 \times 10^8/\text{cm}^2$ or below is formed on a base made of a sapphire single crystal, etc., to fabricate an epitaxial base substrate. Then, a III nitride underfilm is formed on the III nitride buffer film, to fabricate an epitaxial substrate.

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